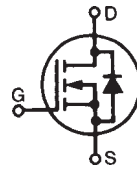


## Polar™ Power MOSFET

## IXTK120N25P

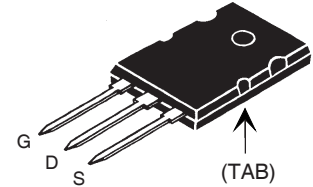
N-Channel Enhancement Mode  
Avalanche Rated  
Fast Intrinsic Diode



$$\begin{aligned} V_{DSS} &= 250V \\ I_{D25} &= 120A \\ R_{DS(on)} &\leq 24m\Omega \end{aligned}$$

| Symbol     | Test Conditions                                                          | Maximum Ratings |                  |
|------------|--------------------------------------------------------------------------|-----------------|------------------|
| $V_{DSS}$  | $T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$                          | 250             | V                |
| $V_{DGR}$  | $T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$ , $R_{GS} = 1M\Omega$    | 250             | V                |
| $V_{GSS}$  | Continuous                                                               | $\pm 20$        | V                |
| $V_{GSM}$  | Transient                                                                | $\pm 30$        | V                |
| $I_{D25}$  | $T_C = 25^\circ\text{C}$                                                 | 120             | A                |
| $I_{LRMS}$ | Terminal Current Limit                                                   | 75              | A                |
| $I_{DM}$   | $T_C = 25^\circ\text{C}$ , Pulse Width Limited by $T_{JM}$               | 300             | A                |
| $I_A$      | $T_C = 25^\circ\text{C}$                                                 | 60              | A                |
| $E_{AS}$   | $T_C = 25^\circ\text{C}$                                                 | 2.5             | J                |
| $dV/dt$    | $I_S \leq I_{DM}$ , $V_{DD} \leq V_{DSS}$ , $T_J \leq 150^\circ\text{C}$ | 10              | V/ns             |
| $P_D$      | $T_C = 25^\circ\text{C}$                                                 | 700             | W                |
| $T_J$      |                                                                          | -55 ... +150    | $^\circ\text{C}$ |
| $T_{JM}$   |                                                                          | 150             | $^\circ\text{C}$ |
| $T_{stg}$  |                                                                          | -55 ... +150    | $^\circ\text{C}$ |
| $T_L$      | 1.6mm (0.062 in.) from Case for 10s                                      | 300             | $^\circ\text{C}$ |
| $T_{SOLD}$ | Plastic Body for 10s                                                     | 260             | $^\circ\text{C}$ |
| $M_d$      | Mounting Torque                                                          | 1.13/10         | Nm/lb.in.        |
| Weight     | TO-264                                                                   | 10              | g                |

### TO-264



G = Gate      D = Drain  
S = Source      TAB = Drain

### Features

- International Standard Package
- Fast Intrinsic Diode
- Avalanche Rated
- Low Package Inductance

### Advantages

- Easy to Mount
- Space Savings
- High Power Density

### Applications

- Switched-Mode and Resonant-Mode Power Supplies
- DC-DC Converters
- Laser Drivers
- AC and DC Motor Drives
- Robotics and Servo Controls

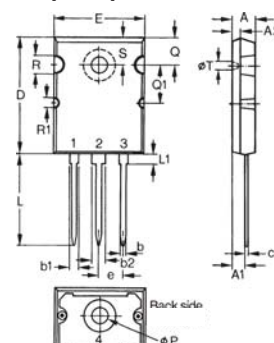
| Symbol       | Test Conditions<br>( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified) | Characteristic Values |      |                           |
|--------------|-----------------------------------------------------------------------------|-----------------------|------|---------------------------|
|              |                                                                             | Min.                  | Typ. | Max.                      |
| $BV_{DSS}$   | $V_{GS} = 0V$ , $I_D = 250\mu A$                                            | 250                   |      | V                         |
| $V_{GS(th)}$ | $V_{DS} = V_{GS}$ , $I_D = 500\mu A$                                        | 2.5                   |      | 5.0 V                     |
| $I_{GSS}$    | $V_{GS} = \pm 20V$ , $V_{DS} = 0V$                                          |                       |      | $\pm 200$ nA              |
| $I_{DSS}$    | $V_{DS} = V_{DSS}$ , $V_{GS} = 0V$<br>$T_J = 125^\circ\text{C}$             |                       |      | 25 $\mu A$<br>250 $\mu A$ |
| $R_{DS(on)}$ | $V_{GS} = 10V$ , $I_D = 0.5 \cdot I_{D25}$ , Note 1                         |                       | 19   | 24 m $\Omega$             |

| Symbol       | Test Conditions<br>( $T_J = 25^\circ\text{C}$ Unless Otherwise Specified)                                                                            | Characteristic Values |      |                        |
|--------------|------------------------------------------------------------------------------------------------------------------------------------------------------|-----------------------|------|------------------------|
|              |                                                                                                                                                      | Min.                  | Typ. | Max.                   |
| $g_{fs}$     | $V_{DS} = 10\text{V}$ , $I_D = 0.5 \cdot I_{D25}$ , Note 1                                                                                           | 45                    | 70   | S                      |
| $C_{iss}$    | $V_{GS} = 0\text{V}$ , $V_{DS} = 25\text{V}$ , $f = 1\text{MHz}$                                                                                     |                       | 8700 | nF                     |
| $C_{oss}$    |                                                                                                                                                      |                       | 1300 | pF                     |
| $C_{rss}$    |                                                                                                                                                      |                       | 240  | pF                     |
| $t_{d(on)}$  | <b>Resistive Switching Times</b><br>$V_{GS} = 10\text{V}$ , $V_{DS} = 0.5 \cdot V_{DSS}$ , $I_D = 0.5 \cdot I_{D25}$<br>$R_G = 3.3\Omega$ (External) |                       | 30   | ns                     |
| $t_r$        |                                                                                                                                                      |                       | 33   | ns                     |
| $t_{d(off)}$ |                                                                                                                                                      |                       | 130  | ns                     |
| $t_f$        |                                                                                                                                                      |                       | 33   | ns                     |
| $Q_{g(on)}$  | $V_{GS} = 10\text{V}$ , $V_{DS} = 0.5 \cdot V_{DSS}$ , $I_D = 0.5 \cdot I_{D25}$                                                                     |                       | 185  | nC                     |
| $Q_{gs}$     |                                                                                                                                                      |                       | 50   | nC                     |
| $Q_{gd}$     |                                                                                                                                                      |                       | 80   | nC                     |
| $R_{thJC}$   |                                                                                                                                                      |                       |      | $0.18^\circ\text{C/W}$ |
| $R_{thCK}$   |                                                                                                                                                      |                       | 0.15 | $^\circ\text{C/W}$     |

## Source-Drain Diode

| Symbol   | Test Conditions<br>( $T_J = 25^\circ\text{C}$ Unless Otherwise Specified)                             | Characteristic Values |      |               |
|----------|-------------------------------------------------------------------------------------------------------|-----------------------|------|---------------|
|          |                                                                                                       | Min.                  | Typ. | Max.          |
| $I_S$    | $V_{GS} = 0\text{V}$                                                                                  |                       |      | 120 A         |
| $I_{SM}$ | Repetitive, Pulse Width Limited by $T_{JM}$                                                           |                       |      | 300 A         |
| $V_{SD}$ | $I_F = 120\text{A}$ , $V_{GS} = 0\text{V}$                                                            |                       |      | 1.5 V         |
| $t_{rr}$ | $I_F = 25\text{A}$ , $-di/dt = 100\text{A}/\mu\text{s}$<br>$V_R = 100\text{V}$ , $V_{GS} = 0\text{V}$ |                       | 200  | ns            |
| $Q_{RM}$ |                                                                                                       |                       | 3.0  | $\mu\text{C}$ |
| $I_{RM}$ |                                                                                                       |                       | 8.0  | A             |

## TO-264 (IXTK) Outline



| Dim. | Millimeter |       | Inches   |       |
|------|------------|-------|----------|-------|
|      | Min.       | Max.  | Min.     | Max.  |
| A    | 4.82       | 5.13  | .190     | .202  |
| A1   | 2.54       | 2.89  | .100     | .114  |
| A2   | 2.00       | 2.10  | .079     | .083  |
| b    | 1.12       | 1.42  | .044     | .056  |
| b1   | 2.39       | 2.69  | .094     | .106  |
| b2   | 2.90       | 3.09  | .114     | .122  |
| c    | 0.53       | 0.83  | .021     | .033  |
| D    | 25.91      | 26.16 | 1.020    | 1.030 |
| E    | 19.81      | 19.96 | .780     | .786  |
| e    | 5.46 BSC   |       | .215 BSC |       |
| J    | 0.00       | 0.25  | .000     | .010  |
| K    | 0.00       | 0.25  | .000     | .010  |
| L    | 20.32      | 20.83 | .800     | .820  |
| L1   | 2.29       | 2.59  | .090     | .102  |
| P    | 3.17       | 3.66  | .125     | .144  |
| Q    | 6.07       | 6.27  | .239     | .247  |
| Q1   | 8.38       | 8.69  | .330     | .342  |
| R    | 3.81       | 4.32  | .150     | .170  |
| R1   | 1.78       | 2.29  | .070     | .090  |
| S    | 6.04       | 6.30  | .238     | .248  |
| T    | 1.57       | 1.83  | .062     | .072  |

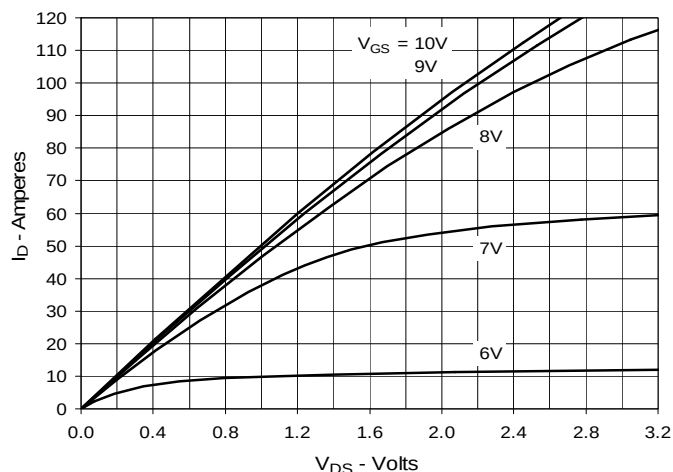
Note 1: Pulse Test,  $t \leq 300\mu\text{s}$ ; Duty Cycle,  $d \leq 2\%$ .

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

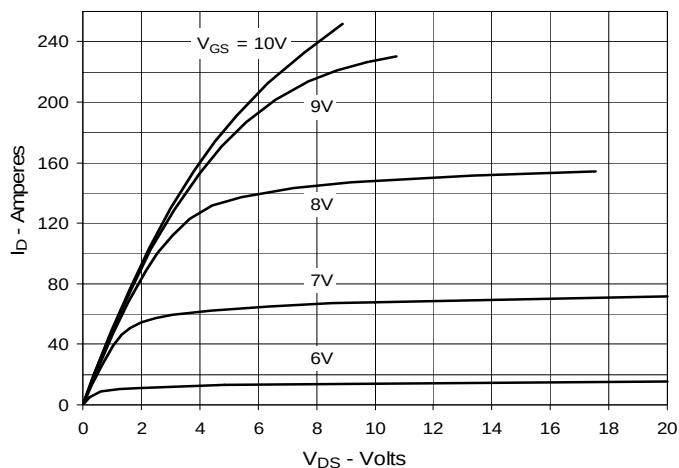
IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

|           |           |           |           |              |              |              |              |              |             |
|-----------|-----------|-----------|-----------|--------------|--------------|--------------|--------------|--------------|-------------|
| 4,835,592 | 4,931,844 | 5,049,961 | 5,237,481 | 6,162,665    | 6,404,065 B1 | 6,683,344    | 6,727,585    | 7,005,734 B2 | 7,157,338B2 |
| 4,850,072 | 5,017,508 | 5,063,307 | 5,381,025 | 6,259,123 B1 | 6,534,343    | 6,710,405 B2 | 6,759,692    | 7,063,975 B2 |             |
| 4,881,106 | 5,034,796 | 5,187,117 | 5,486,715 | 6,306,728 B1 | 6,583,505    | 6,710,463    | 6,771,478 B2 | 7,071,537    |             |

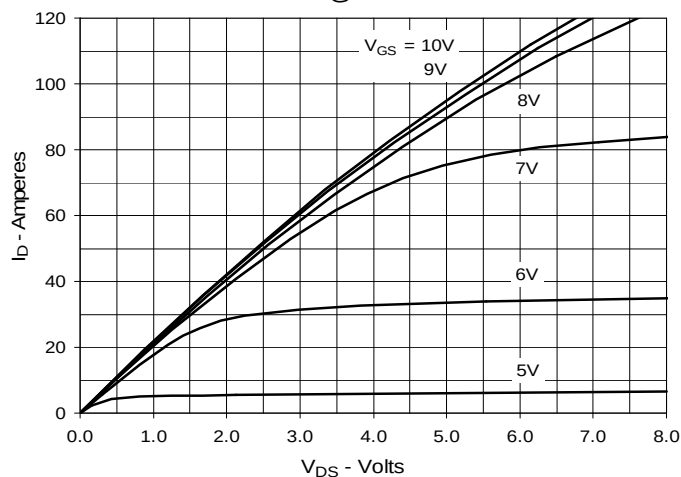
**Fig. 1. Output Characteristics**  
@ 25°C



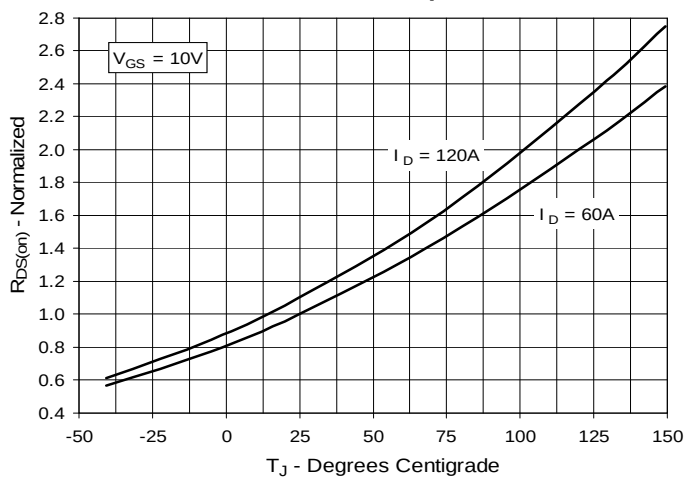
**Fig. 2. Extended Output Characteristics**  
@ 25°C



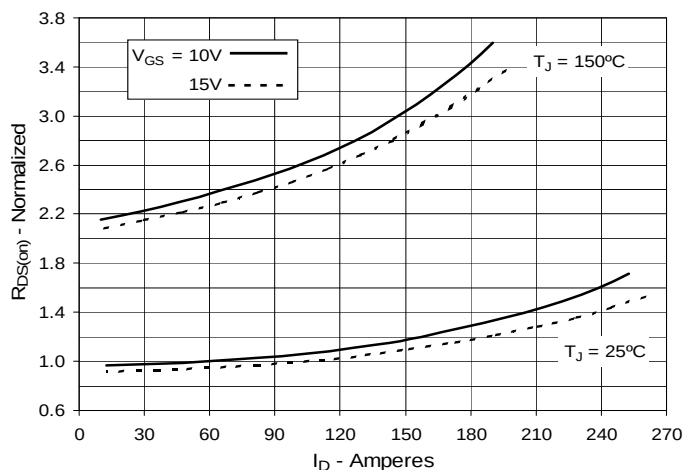
**Fig. 3. Output Characteristics**  
@ 125°C



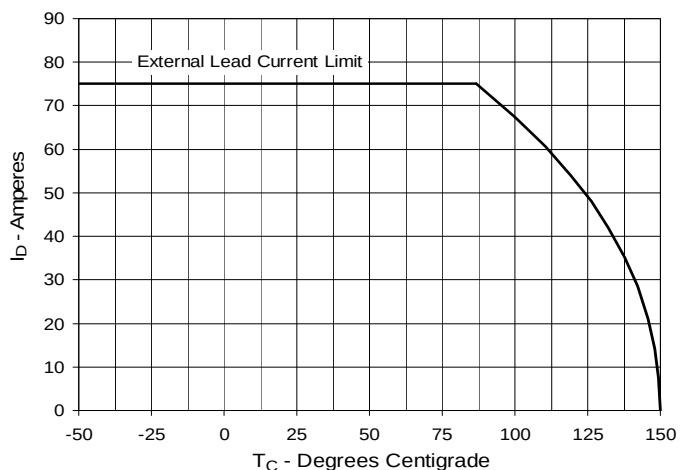
**Fig. 4.  $R_{DS(on)}$  Normalized to  $I_D = 60A$  Value**  
vs. Junction Temperature



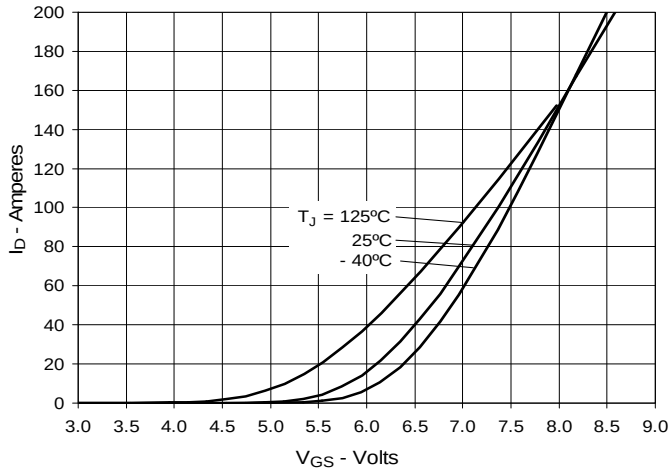
**Fig. 5.  $R_{DS(on)}$  Normalized to  $I_D = 60A$  Value**  
vs. Drain Current



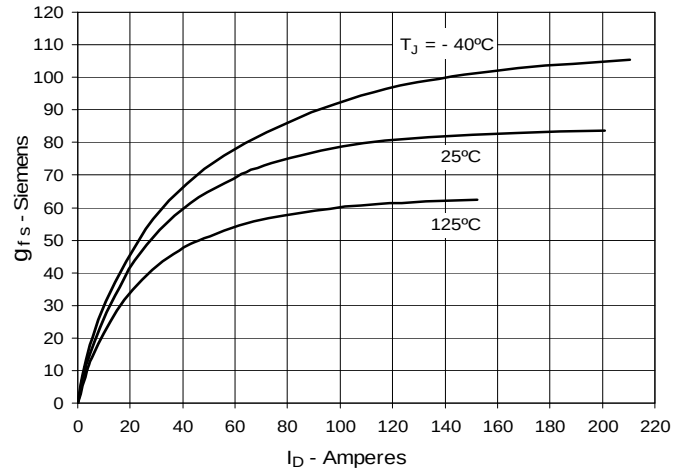
**Fig. 6. Maximum Drain Current vs.**  
Case Temperature



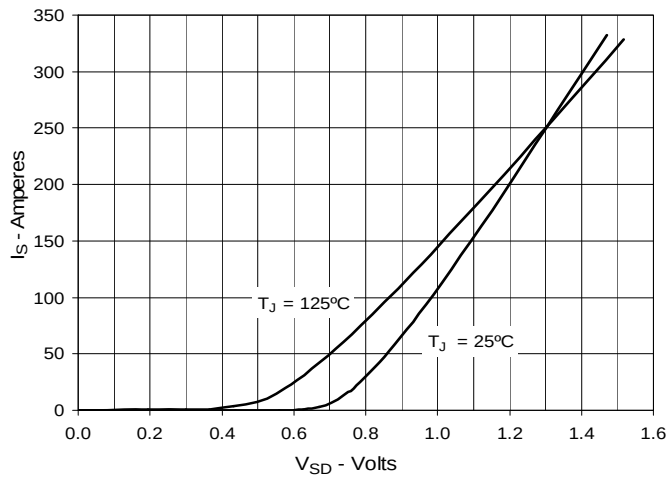
**Fig. 7. Input Admittance**



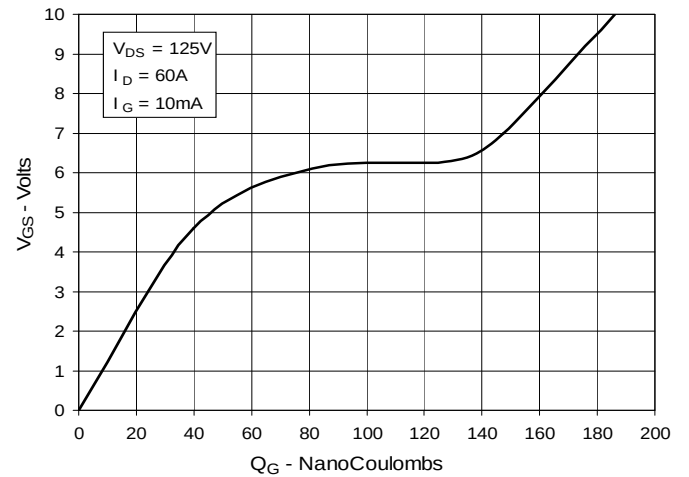
**Fig. 8. Transconductance**



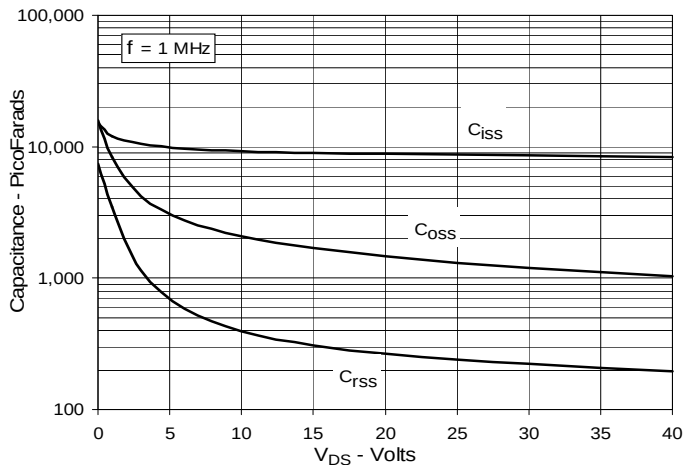
**Fig. 9. Forward Voltage Drop of Intrinsic Diode**



**Fig. 10. Gate Charge**



**Fig. 11. Capacitance**



**Fig. 12. Forward-Bias Safe Operating Area**

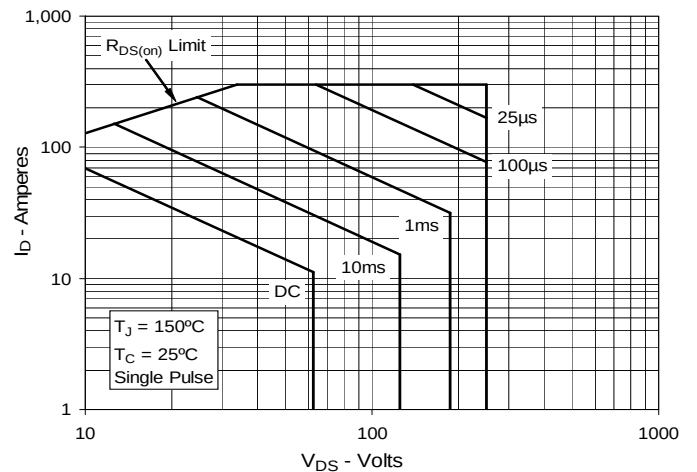
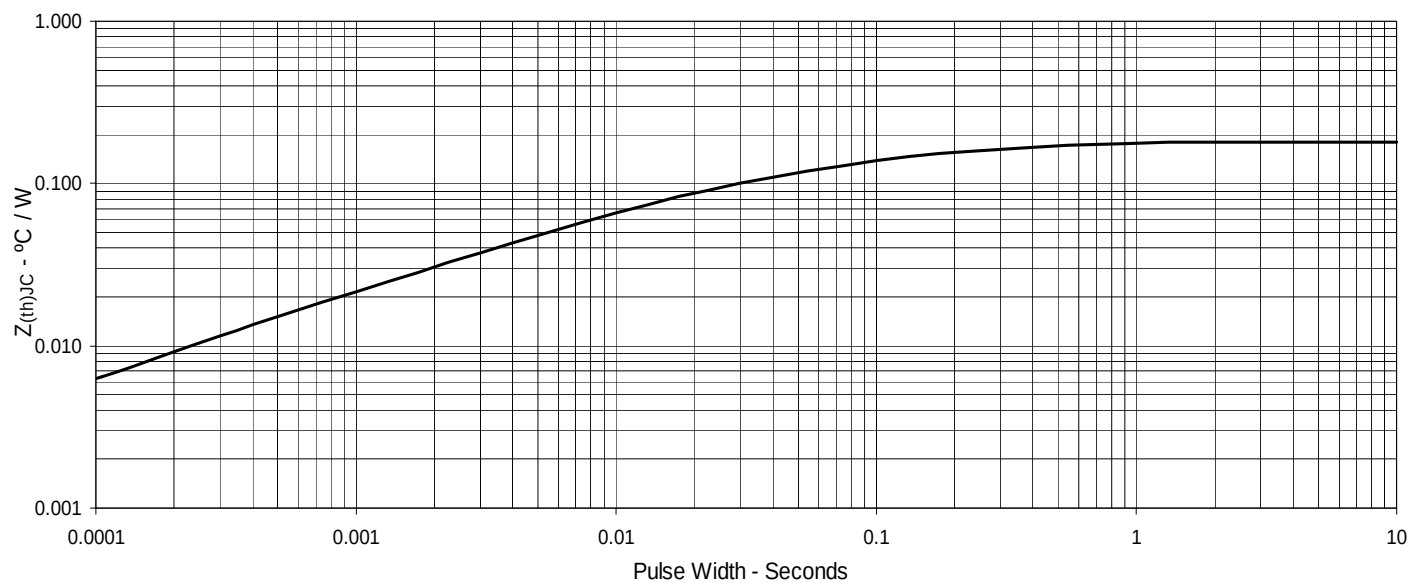


Fig. 13. Maximum Transient Thermal Impedance





---

Disclaimer Notice - Information furnished is believed to be accurate and reliable. However, users should independently evaluate the suitability of and test each product selected for their own applications. Littelfuse products are not designed for, and may not be used in, all applications. Read complete Disclaimer Notice at [www.littelfuse.com/disclaimer-electronics](http://www.littelfuse.com/disclaimer-electronics).